

### D6-7-660-10



#### Application

Laser Projector  
Measuring equipment

#### Property

Wavelength  $\lambda = 660 \text{ nm}$   
Output Power = 10 mW  
Package Type =  $\varnothing 5.6\text{mm}$

#### Introduction

Egismos currently markets AlGaInP based red laser diodes in the 635nm~ 670nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers.

### Laser Diode Key Features

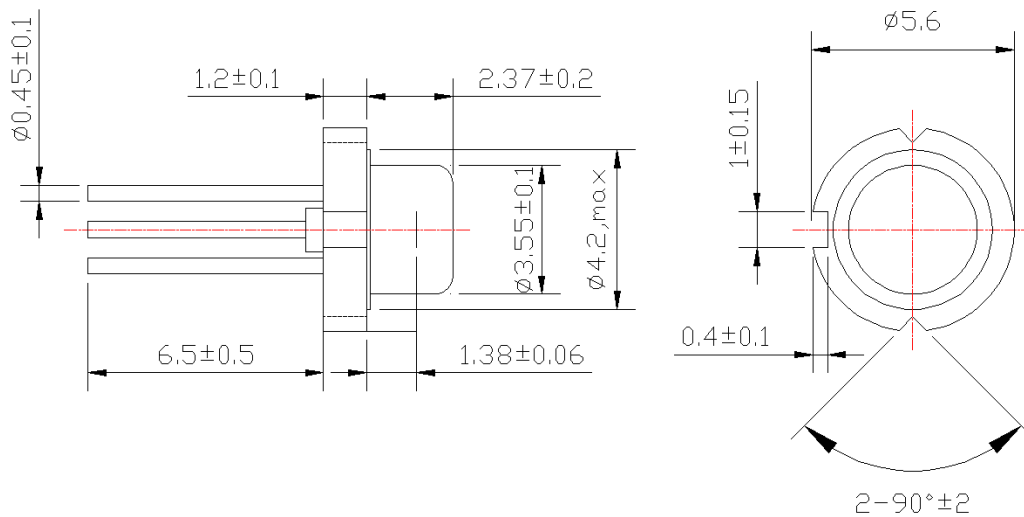
Absolute Maximum Rating at  $T_c=25^\circ\text{C}$

Items	Symbols	Values	Unit
Operating Current power	$P_o$	10	mW
Reverse Voltage	$V_R$	2	V
Operating Temperature	$T_{case}$	-10~+70	$^\circ\text{C}$
Storage Temperature	$T_s$	-40~+85	$^\circ\text{C}$

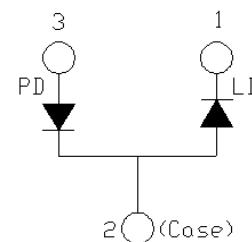
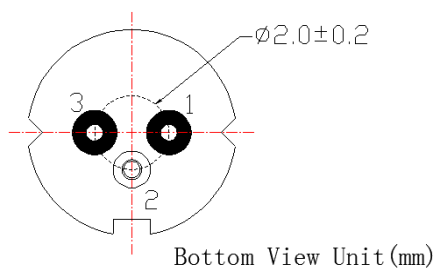
### Electrical and Optical Characteristics at Tc=25°C

Item	Symbols	Min	Typ.	Max.	Unit	Condition
Threshold Current	$I_{th}$	-	20	25	mA	-
Operating Current	$I_{op}$	-	30	35	mA	Po=10mW
Operating Voltage	$V_{op}$	-	2.2	2.5	V	Po=10mW
Peak Wavelength	$\lambda_p$	650	658	665	nm	Po=10mW
Beam Divergence (FWHM)	$\theta_r$	6	8	12	deg	Po=10mW
Beam Divergence (FWHM)	$\theta_{\pm}$	22	28	32	deg	Po=10mW
Monitor Current	$I_m$	0.1	0.25	0.5	mA	Po=10mW

### Package Drawing



### Electrical Connection



Specifications are subject to change without notice.

